

# Zuverlässigkeit und Fehlertoleranz / Dependability and Fault Tolerance

## Chapter 2

# **Faults and Fault Models**

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# Faults- Errors-Defects

## **Specifically for hardware in electronic systems**

Defekt – Defect: Something wrong with the physical structure

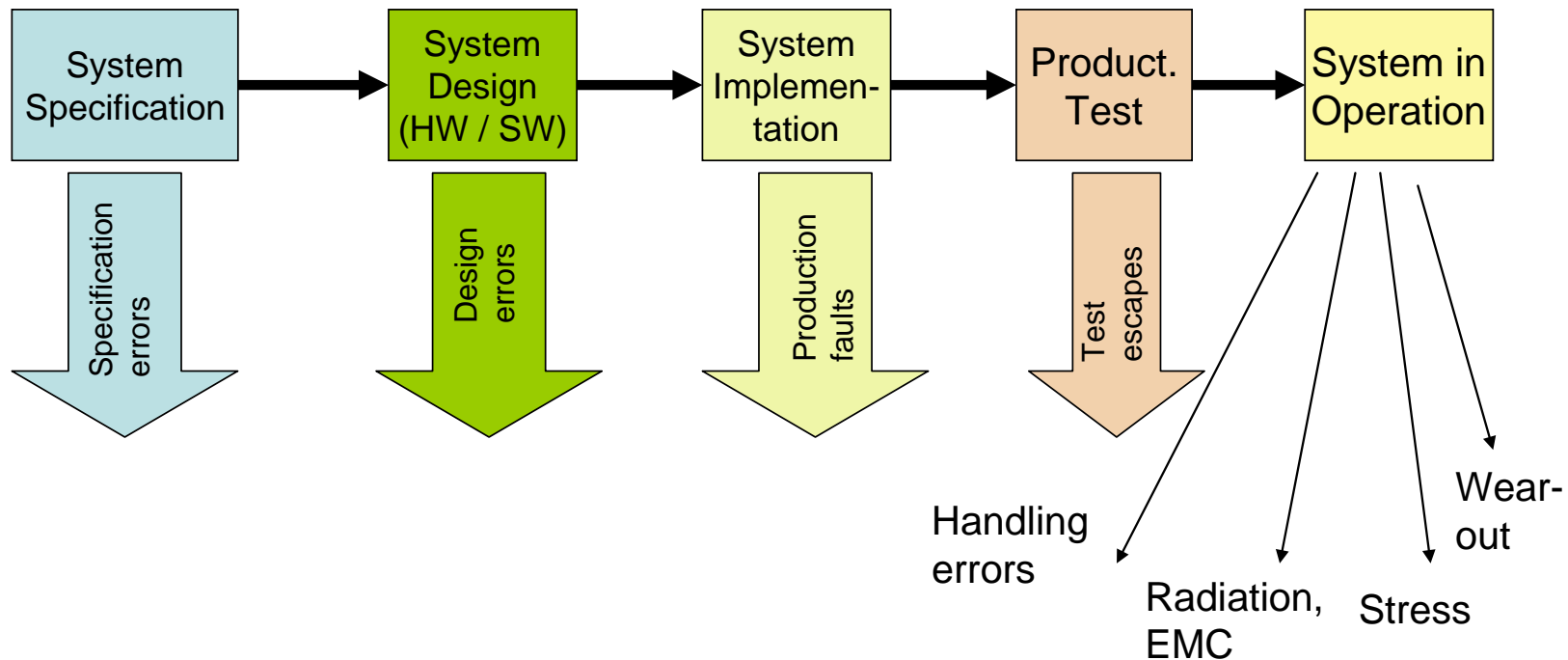
Fehler – Fault: a faulty signal, for example a fault bit, possibly never to appear

Fehler – Error: a faulty signal which becomes visible and may have an effect

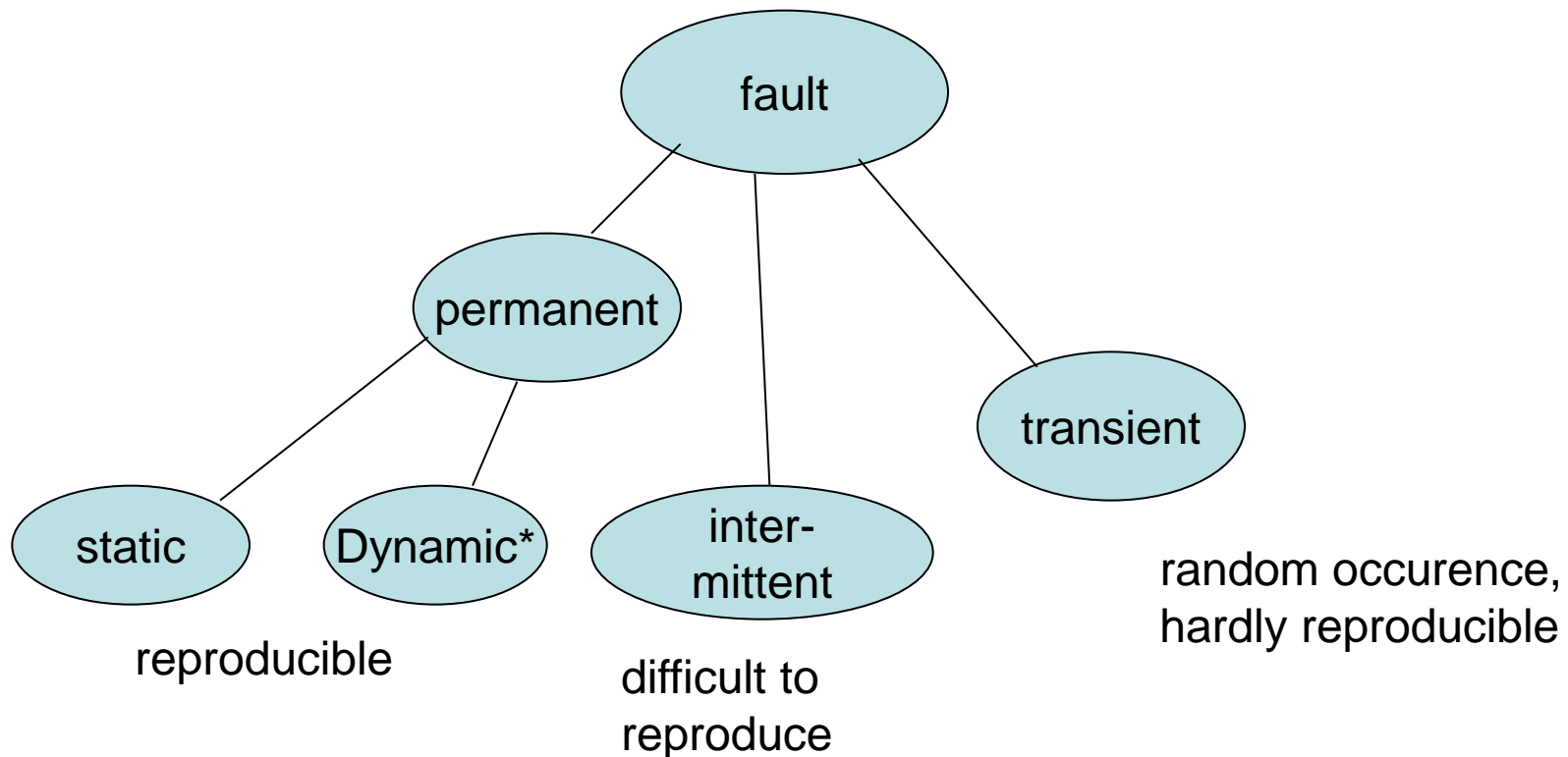
Failure – Versagen: the systems produces an erroneous output with effects

Breakdown - Ausfall: the total function of a system collapses

# Hierarchy of Faults / Errors

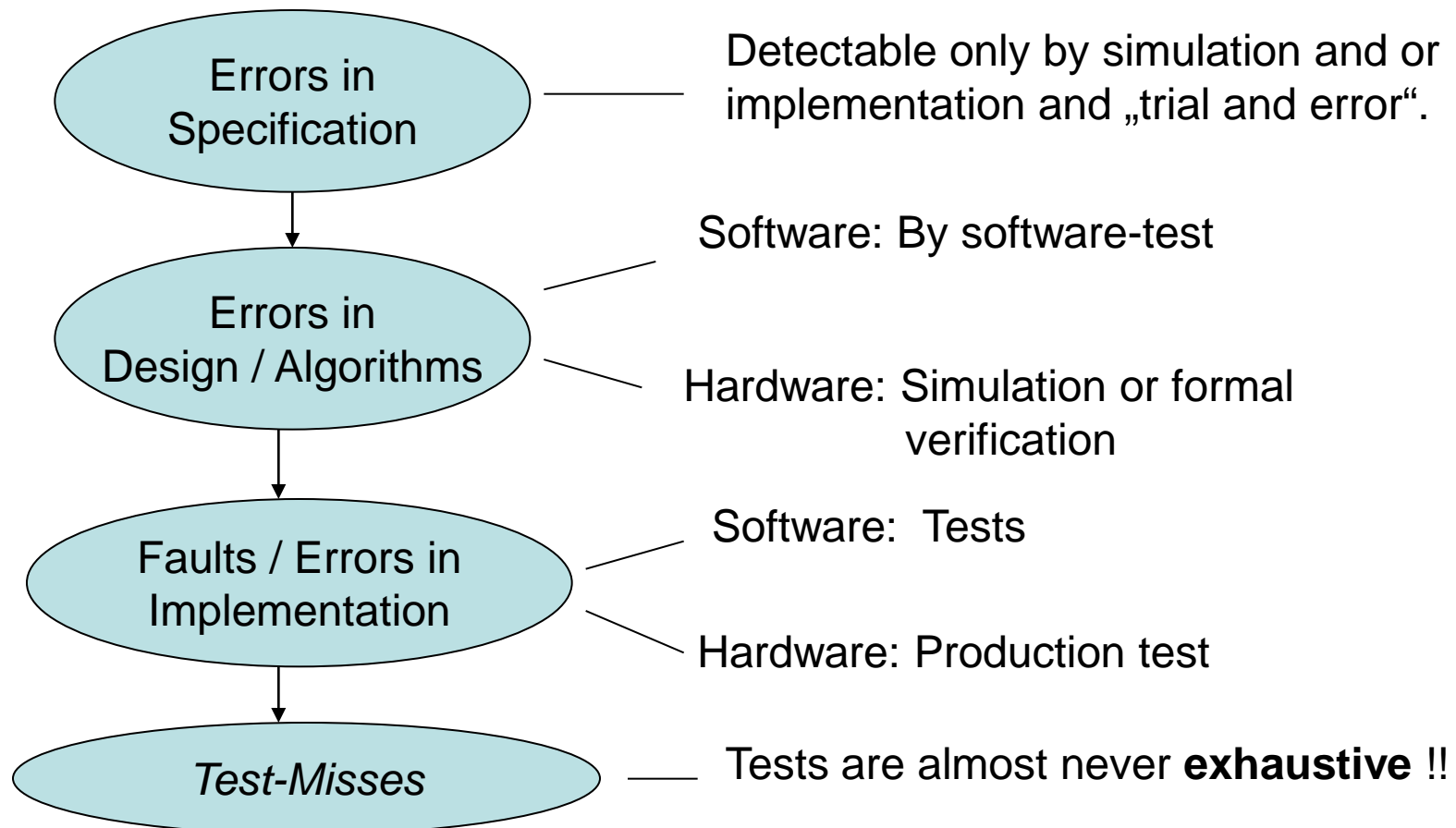


# Types of Faults in Hardware



**\* most important: delay faults**

# Error Mechanisms and Validation



# Fault Behaviour

Errors in specification, in hard- and software design / implementation are **permanent**, unless there is a repair event.

They will not alter themselves during the life time of a system.

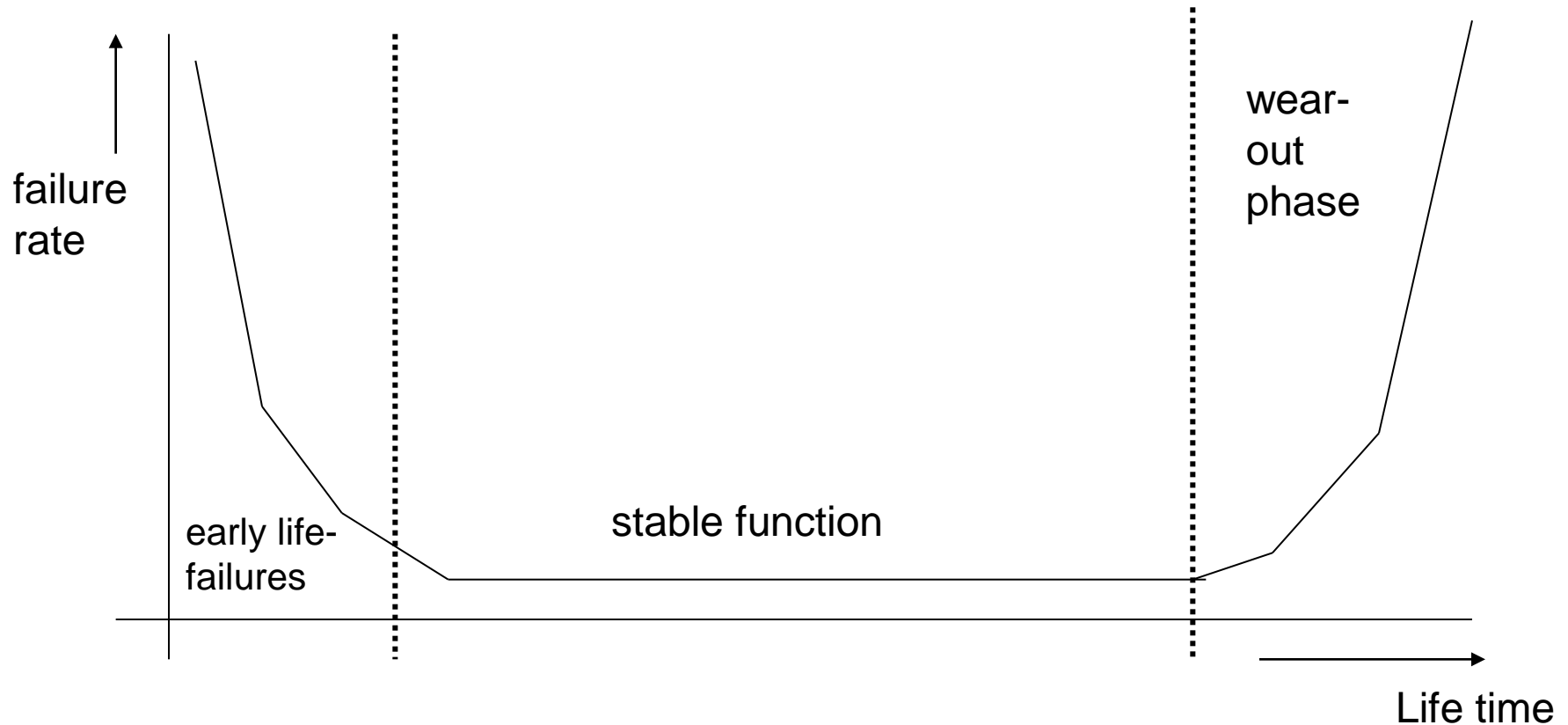
Faults in hardware can be **permanent, transient** or **intermittent**.

Throughout system life time, hardware faults can:

- newly appear (due to stress, aging, radiation, EM coupling)
- disappear (self healing)
- get worse (change from intermittent to permanent).

# Errors / Failures over Time

„bathtub-curve“



# Lifetime / Failure Curve

Early life failures: Hidden defects after production, will produce faults and errors only after receiving some „stress“. Also due to test misses !

Wear-out failures: All mechanical, electrical, electronic devices undergo mechanisms of aging and wear-out.

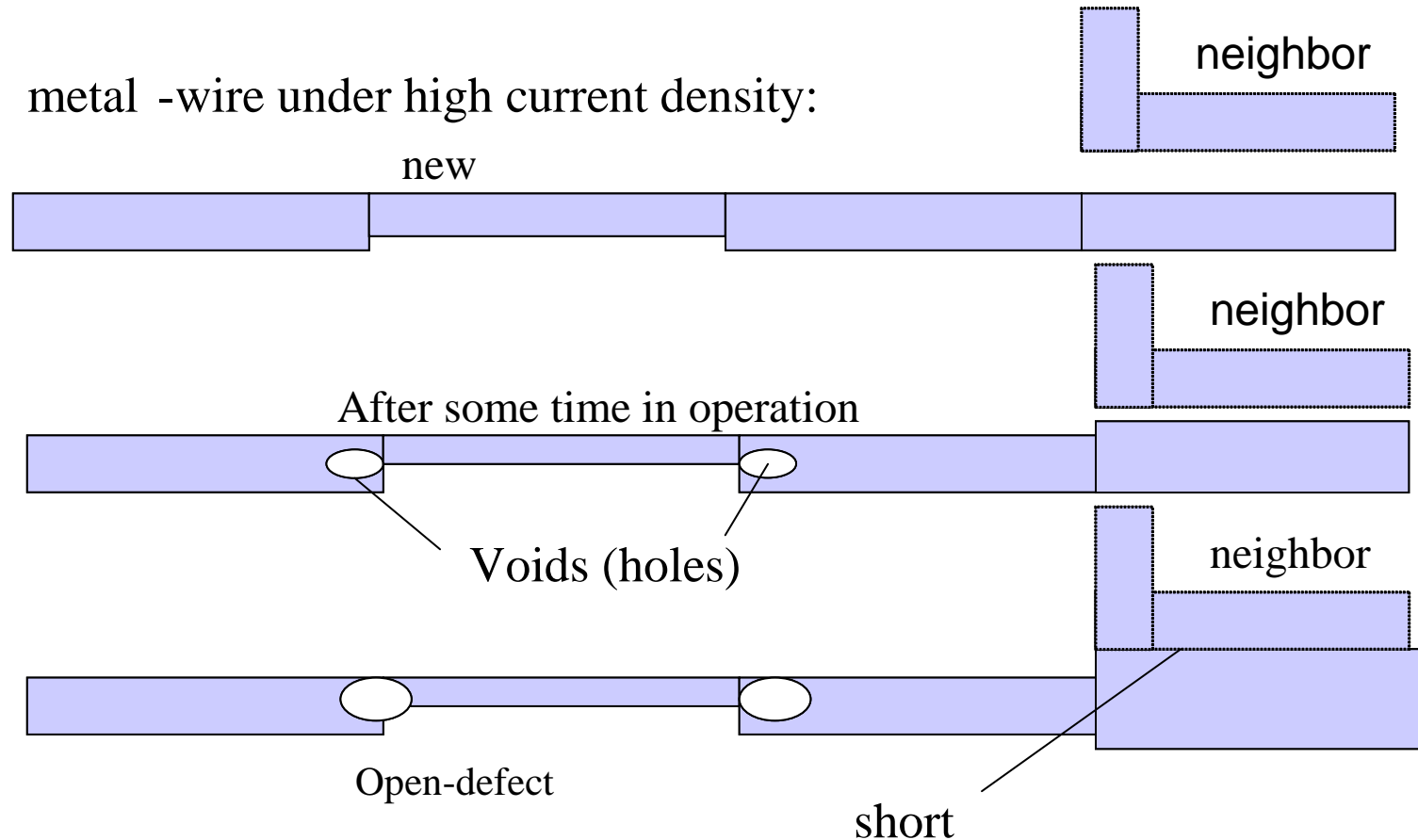
Wear-out : Only in hardware. But software needs processors to run. Strongly depending on temperature !!! Typically, stress grows about exponentially with temperature.

Transient faults: Error density after early life and before wear-out is mainly caused by radiation effects and EM-coupling..



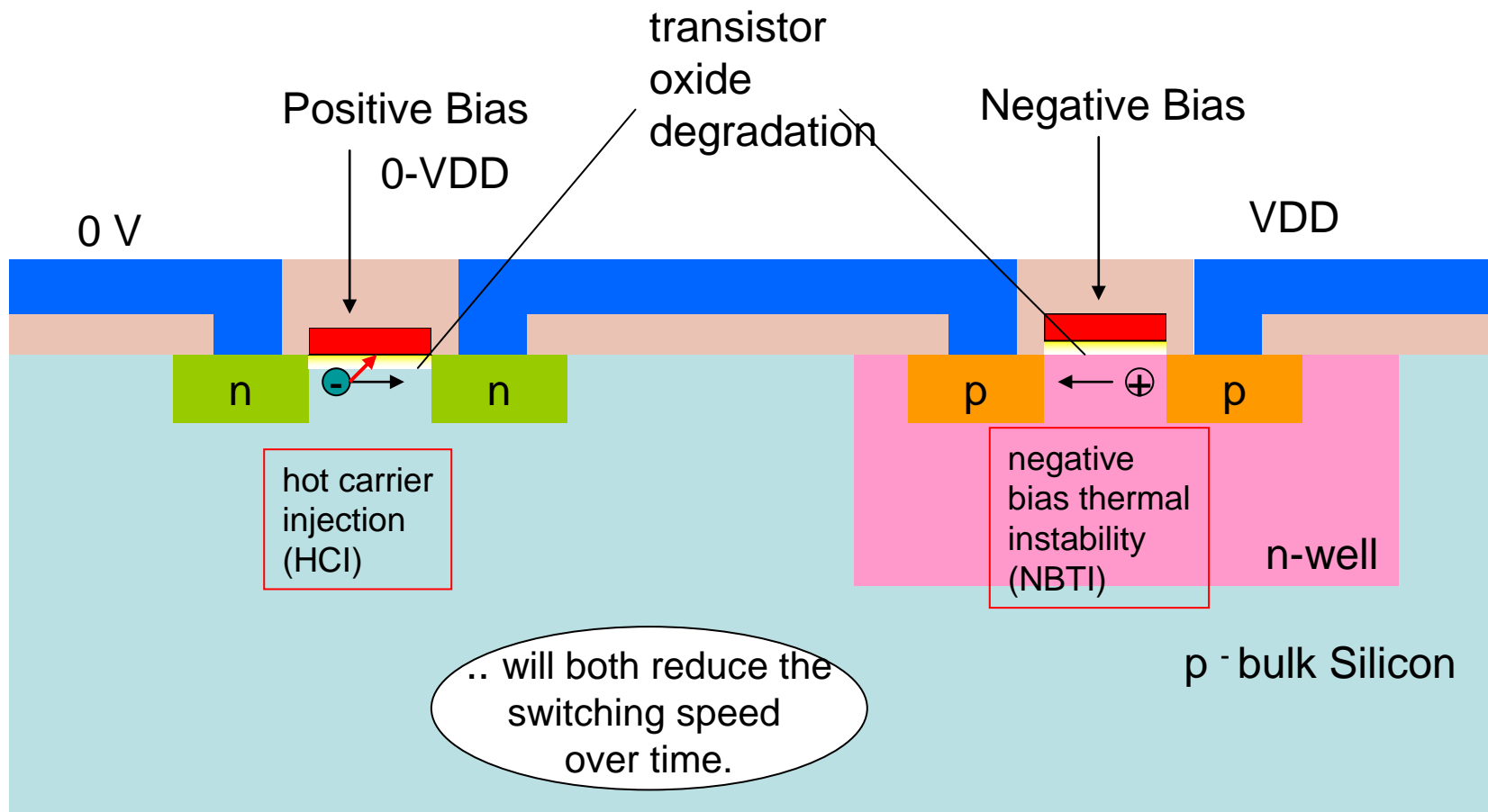
# Metal Migration

metal -wire under high current density:



- Vias are specially prone to such defects
- The effect is reversible by reversing the direction of current flow !

# IC-Fault Mechanisms



# Fault Mechanisms in CMOS ICs

- Hot Carrier Injection (HCI), mainly in n-channel transistors:

High-energy electrons „tunnel“ through the gate-oxide, assemble on the gate and cause modifications of the transistor parameters. A well-known effect technically used for EEPROMs and for FLASH memory !

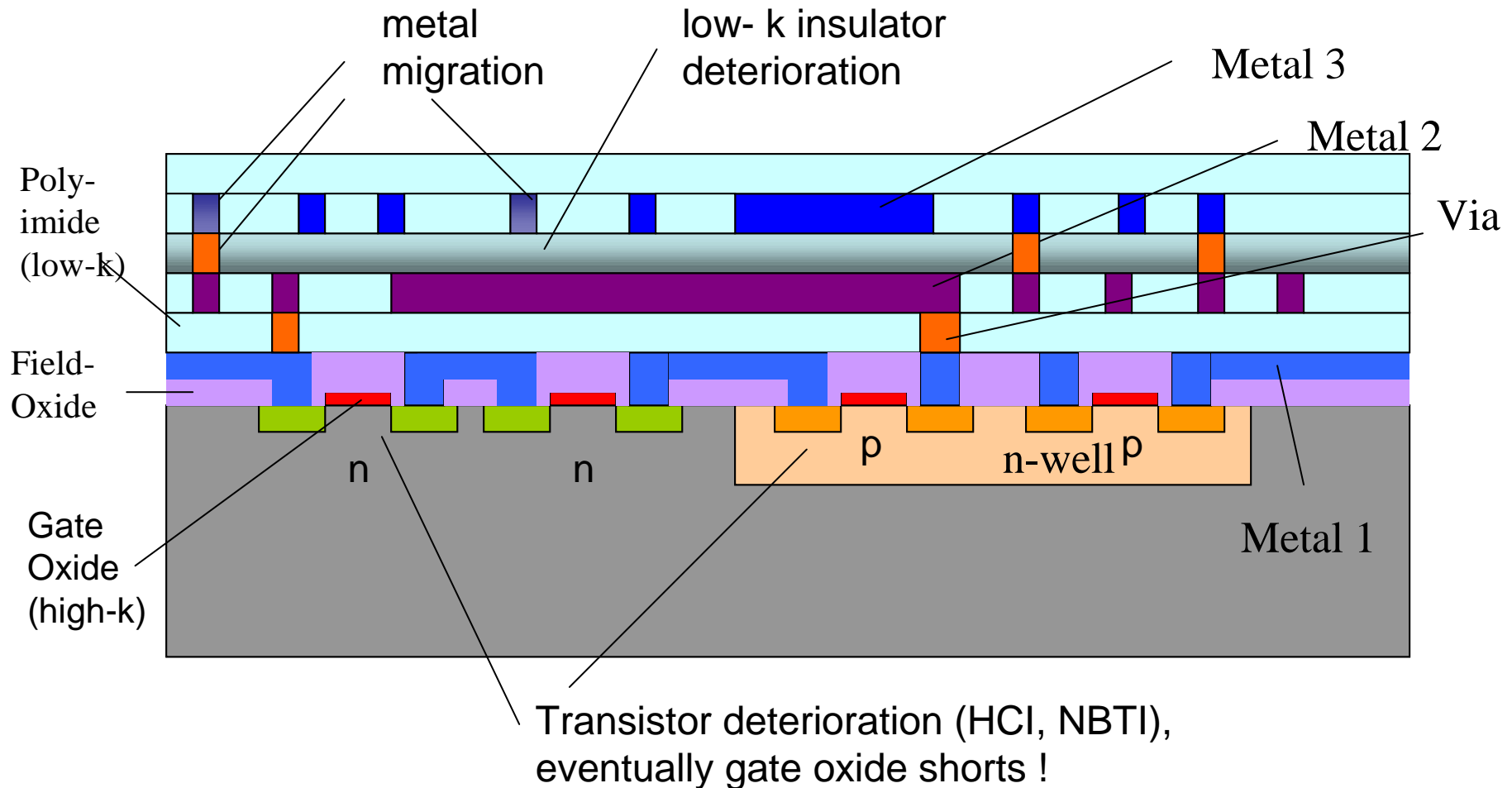
- Negative (positive) bias thermal instability NBTI (PBTI):

With a constant positive / negative bias applied over a longer time, hydrogen ions at the semiconductor / oxide interface migrate in the gate-oxide. This causes variations in the transistor threshold voltage (the voltage between gate-bulk from which it starts conducting). The transistor becomes slower, gate delays increase. The effect is partly reversible. It is much stronger on p-channel (NBTI) than on n-channel transistors (PBTI).

- Dielectric gate rupture:

Thin oxide layers (typically only 3 atoms thick on CMOS gates !) may actually break and cause a non-reversible short between gate and channel of an MOS transistor !

# Wear-Out and Aging

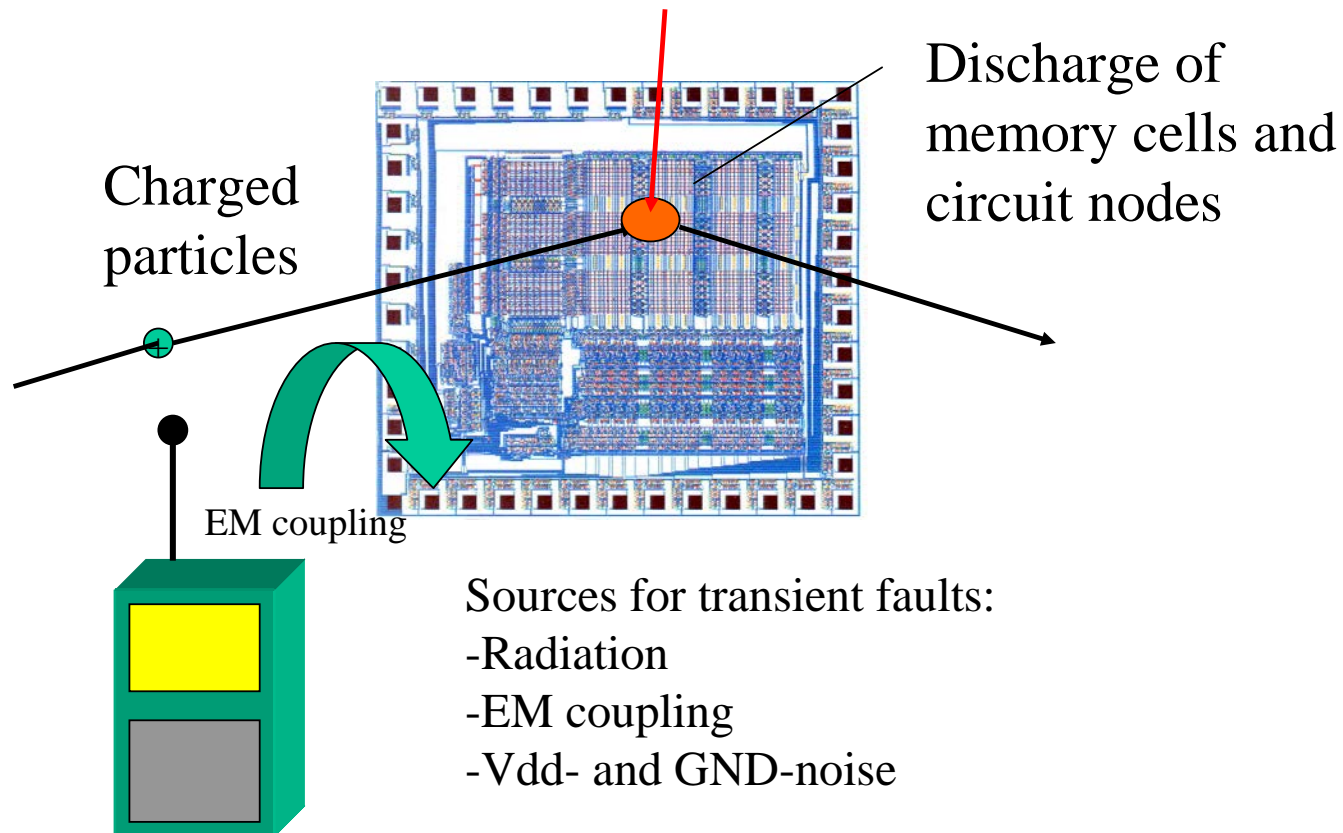


# Important Aging Effects on ICs

- Parameter shifting, mainly increase of  $V_{th}$  (threshold voltage of MOS-transistors) by negative / positive bias thermal instability (NBTI / PBTI) and by hot carrier injection (HIC), tunnelling of electrons through gate oxide (mainly in n-MOS).
- Thinning of lines, creation of voids through metal migration, may also create bridges.
- Break of oxide layers between metal wires (insulators)
- Break of lines due to mechanical stress, also caused by heating
- Break of gate oxide in MOS transistors

*.. with higher specific stress for nano-circuits !! Due to thinner lines and thinner oxide layers !*

# Transient Faults



# Sources of Transient Faults

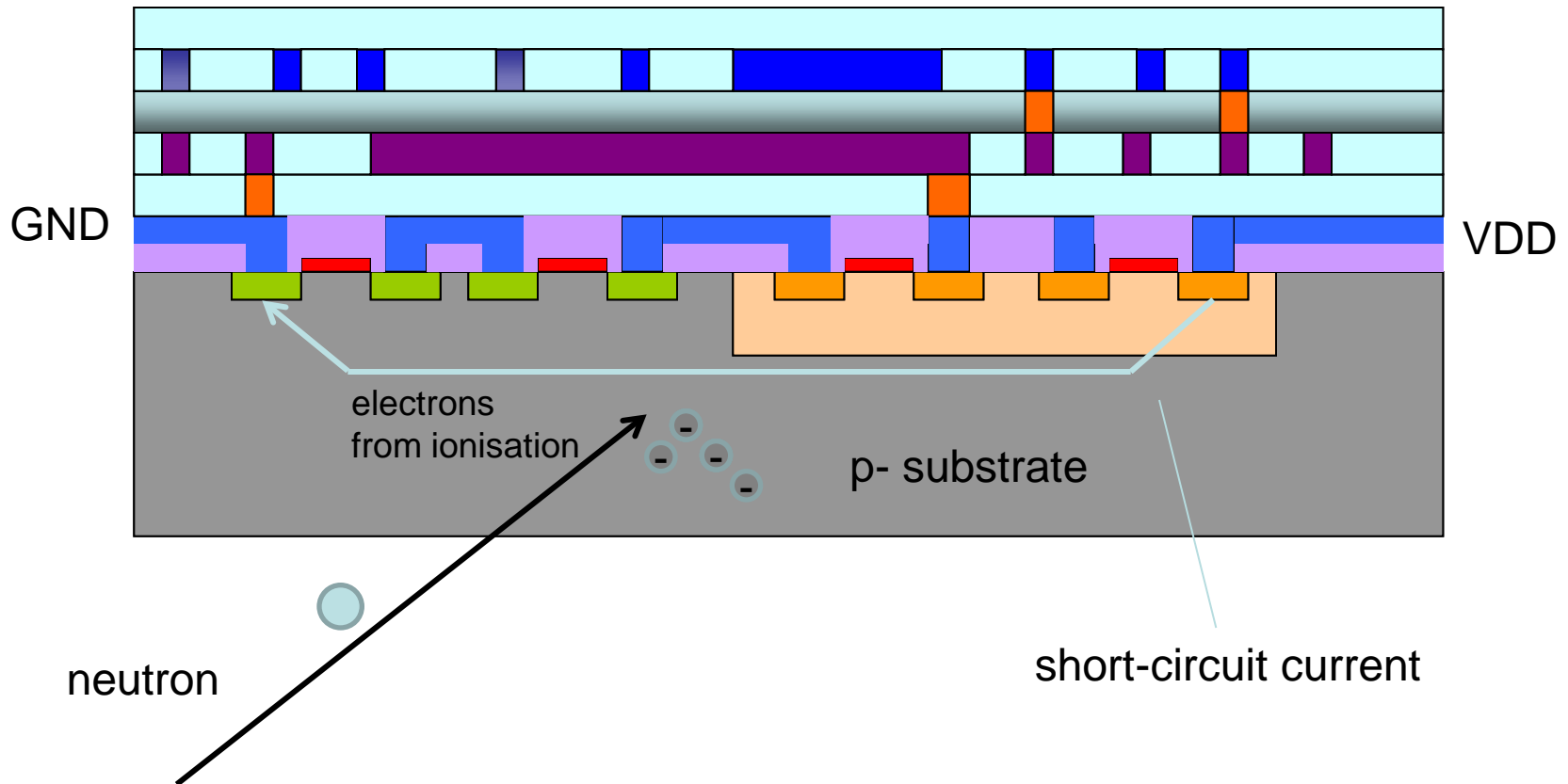
1. **Particle Radiation:** Neutrons, alpha-particles from radioactive decay cause „faulty“ bits als „single even upsets(SEUs) or single event transients (SETs) also as „multi event upsets“ (MEUs) / multi-event transients (METs).

Particle radiation can trigger a break-through of reverse biases p-n-junctions in MOS transistors. „Latch-Up“ is a well known failure process in CMOS-logic which creates a direct VDD- GND-connection, high currents, thermal damage.

2. **Electromagnetic Coupling:** Lines on ICs may act as antennas and „catch“ wireless EM-radiation. Lines on ICs suffer from capacitive coupling of lines, the more the smaller.
3. **VDD / GND Noise:** VDD / GND voltage levels are not stable, but will change with circuit activity. More switching events at the same time cause stress on the VDD-grid and lower voltage locally. Currents on ground nets can also „raise“ GND-voltage !



# Latch-Up





# Error Density in Real Life

**Cray XT5, Oak Ridge, Tennessee, „Jaguar“**

Memory size: 360 terabytes, all ECC\*-protected

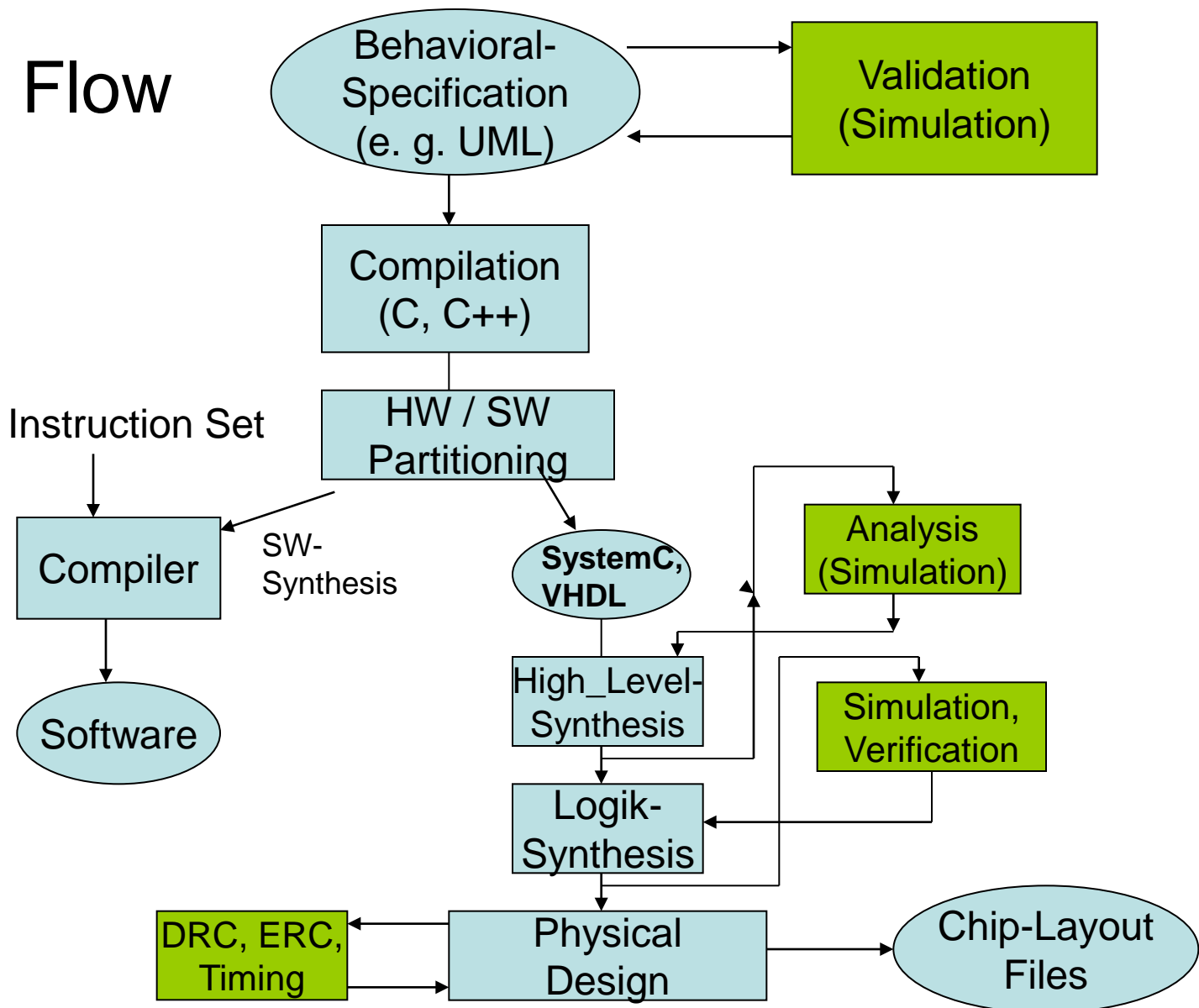
ECC error rate: 350 per minute (single bit errors)  
1 per 24 hours (double bit errors)

*This corresponds to one single bit error on a 1 GByte-memory  
about every 16 hours !*

Radiation- induced „hits“ causing permanent damages were also measured, but  
much less frequently !

\* error correction code

# Design Flow



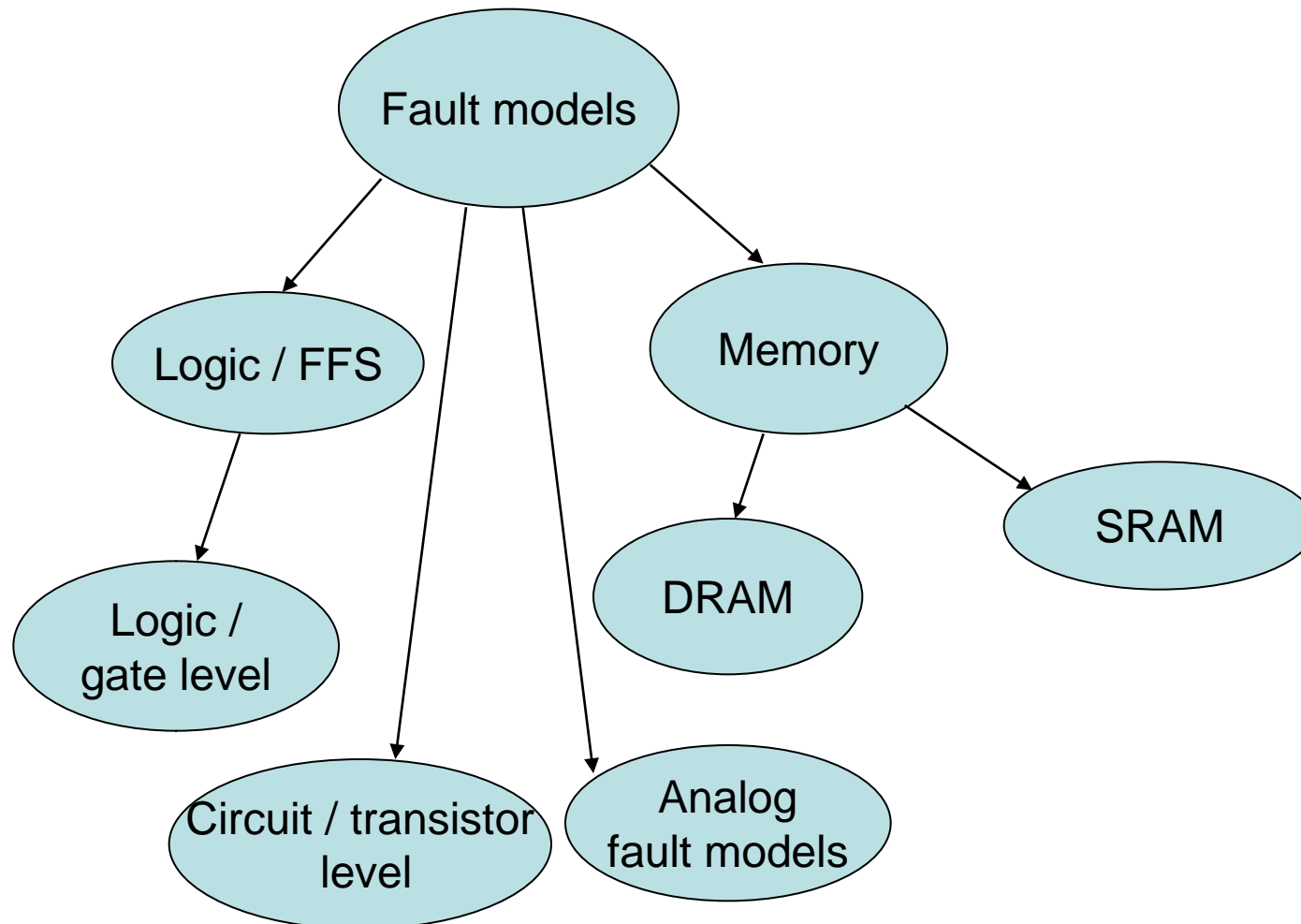
# Simulation auf Fault Behavior

**Fault Simulation:** The fault is „modeled“, mainly at the logic gate level.  
Fault simulations can then effectively simulate the faulty  
(and the good) circuits, often in parallel.

**Fault Injection:** We take a normal simulator at the RT- or gate-level or even  
an FPGA. Then we introduce a fault, e. g. by setting a node  
to „always 0“ and observe the outcome.

Fault injection is the more universal approach, since it does not require  
special models or special tools, but it is much slower.

# Fault Models for Digital Systems

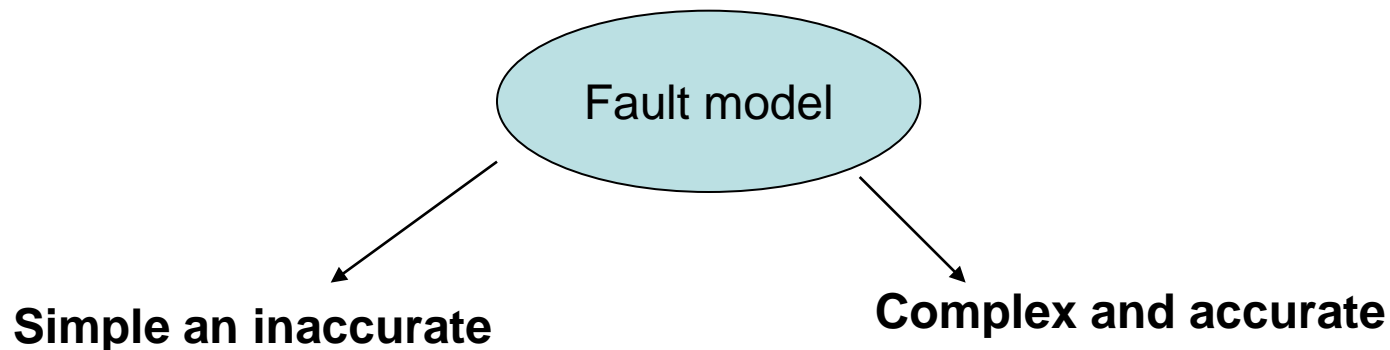


# Hardware Fault Models

The variety of physical defects is large and almost impossible to cover by models and simulation tools. Complexity problem !!!

One common solution is to „simplify“ real faults towards specific types of „abstracted“ faults at the circuit- or logic level.

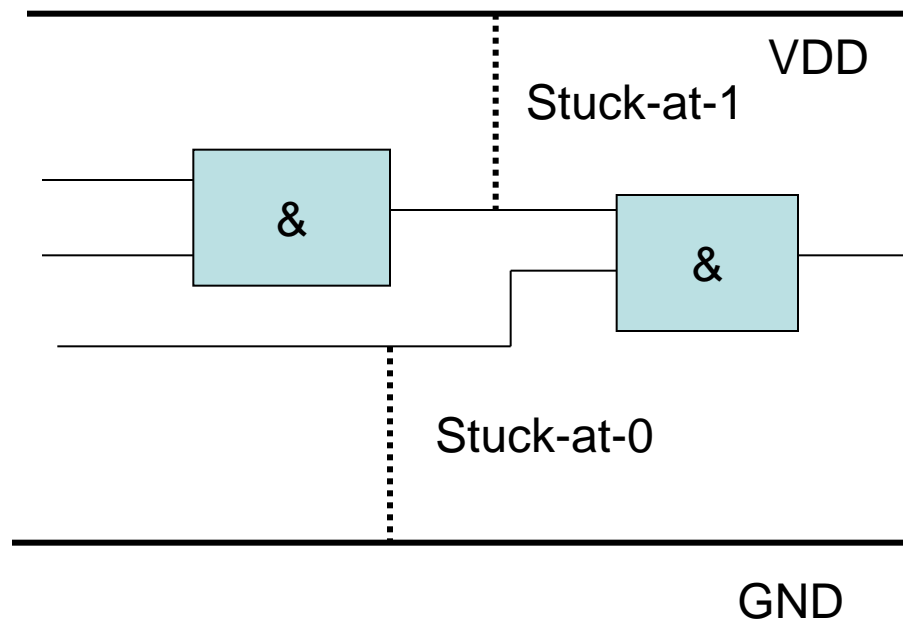
This simplification works only for digital circuits / systems.



Pro: Can manage large  
Complexity in simulation  
Con: May miss real faults

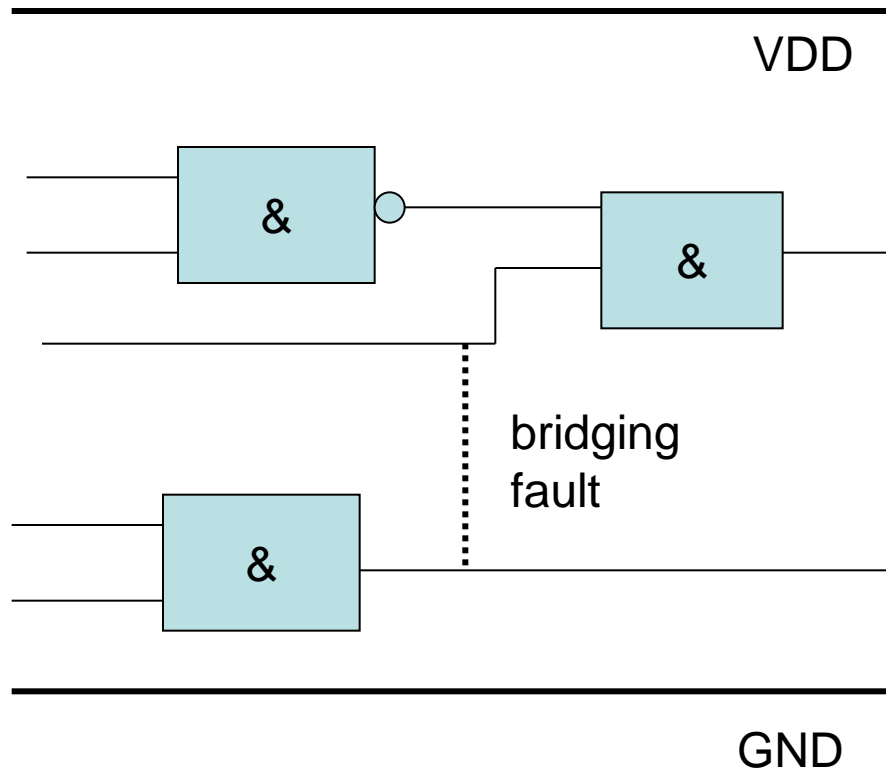
Pro: May catch complex fault behavior  
Con: Complexity of simulation for larger  
circuits explodes.

# Fault Models: Stuck-at-Fault



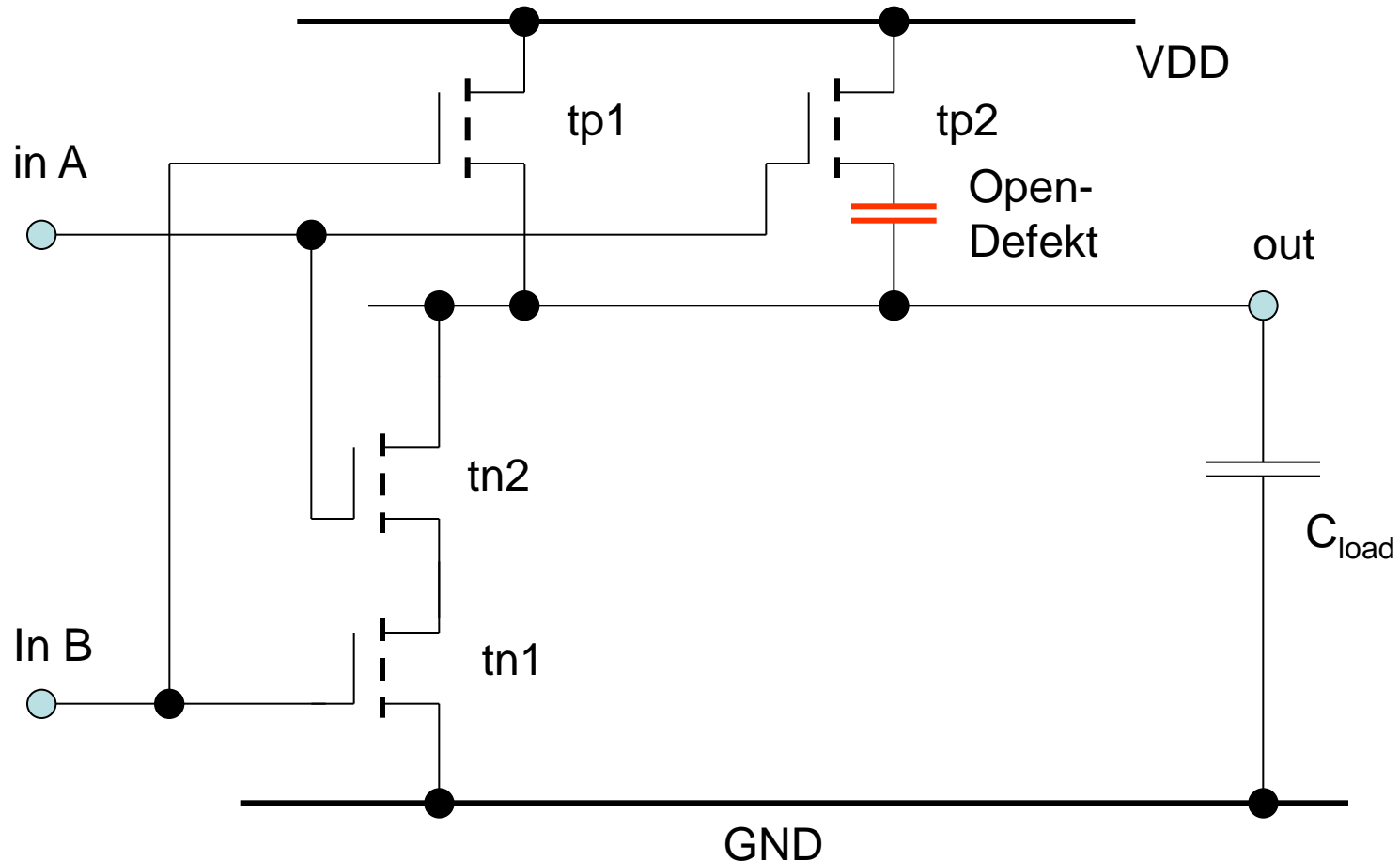
A node in a logic circuit is erroneously fixed at the „VDD“ (1) or the ground (0) potential.

# Bridge Fault



Bridging a signal line to VDD / GND results in a stuck-at 1 / 0 fault. Bridges between signal lines are much more difficult to model at the logic gate level. They may result in voltage levels between VDD / GND or even in feedback in combinational logic. An intermediate voltage level at around VDD/2 may even be taken as „1“ by one fed gate and as „0“ by another one. Byzantine General's Problem !

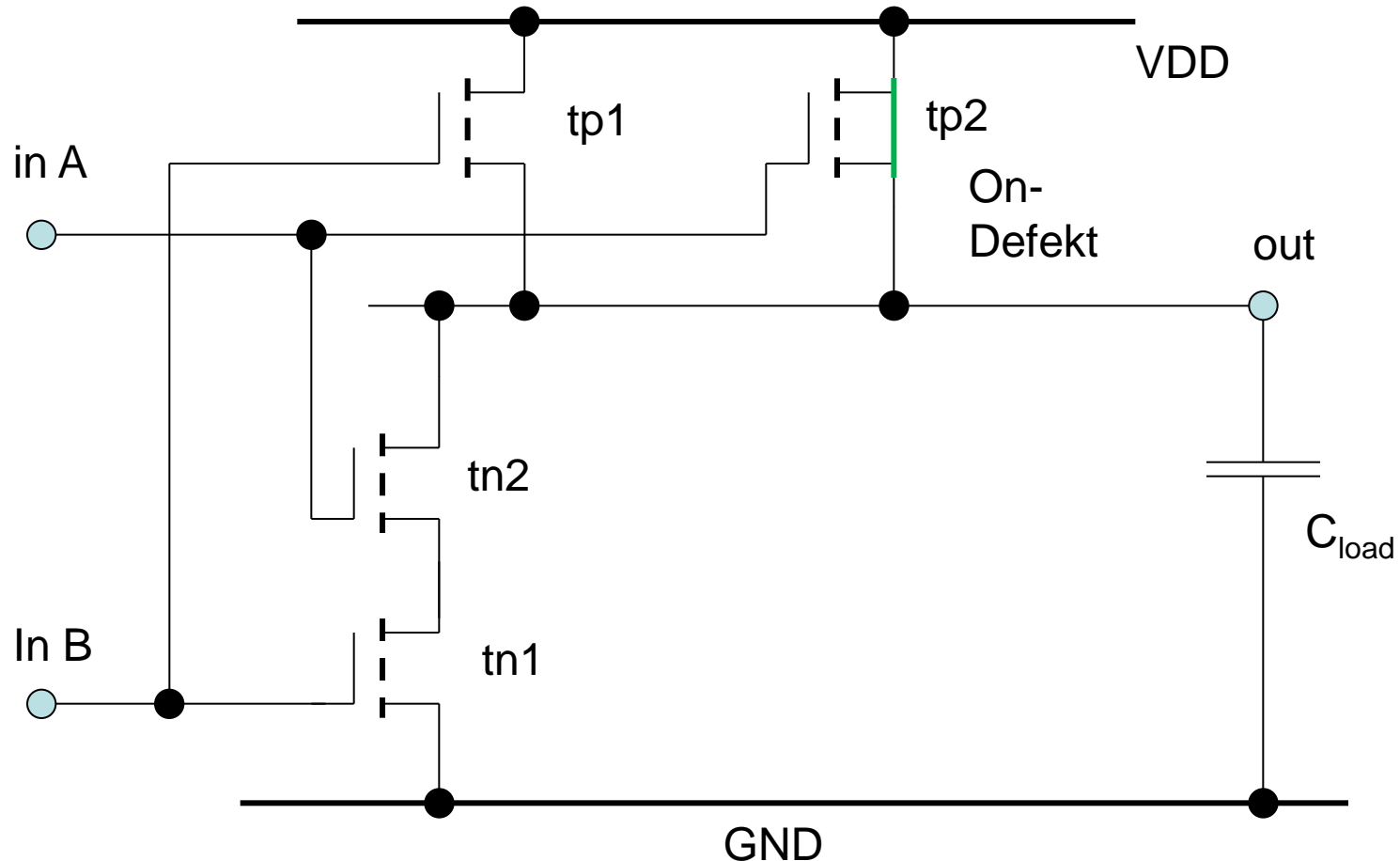
# Stuck-Open-Fault



One transistor is always „non conducting“. Leads to parasitic storage effects !

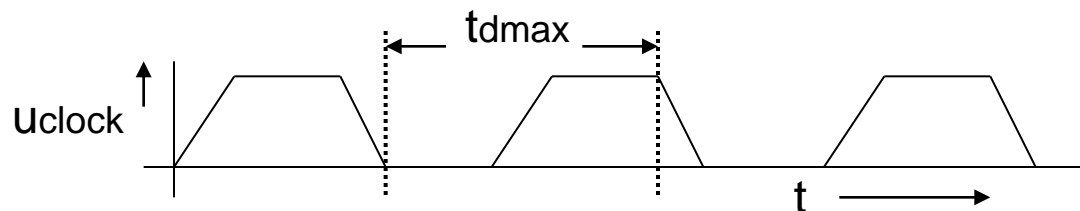
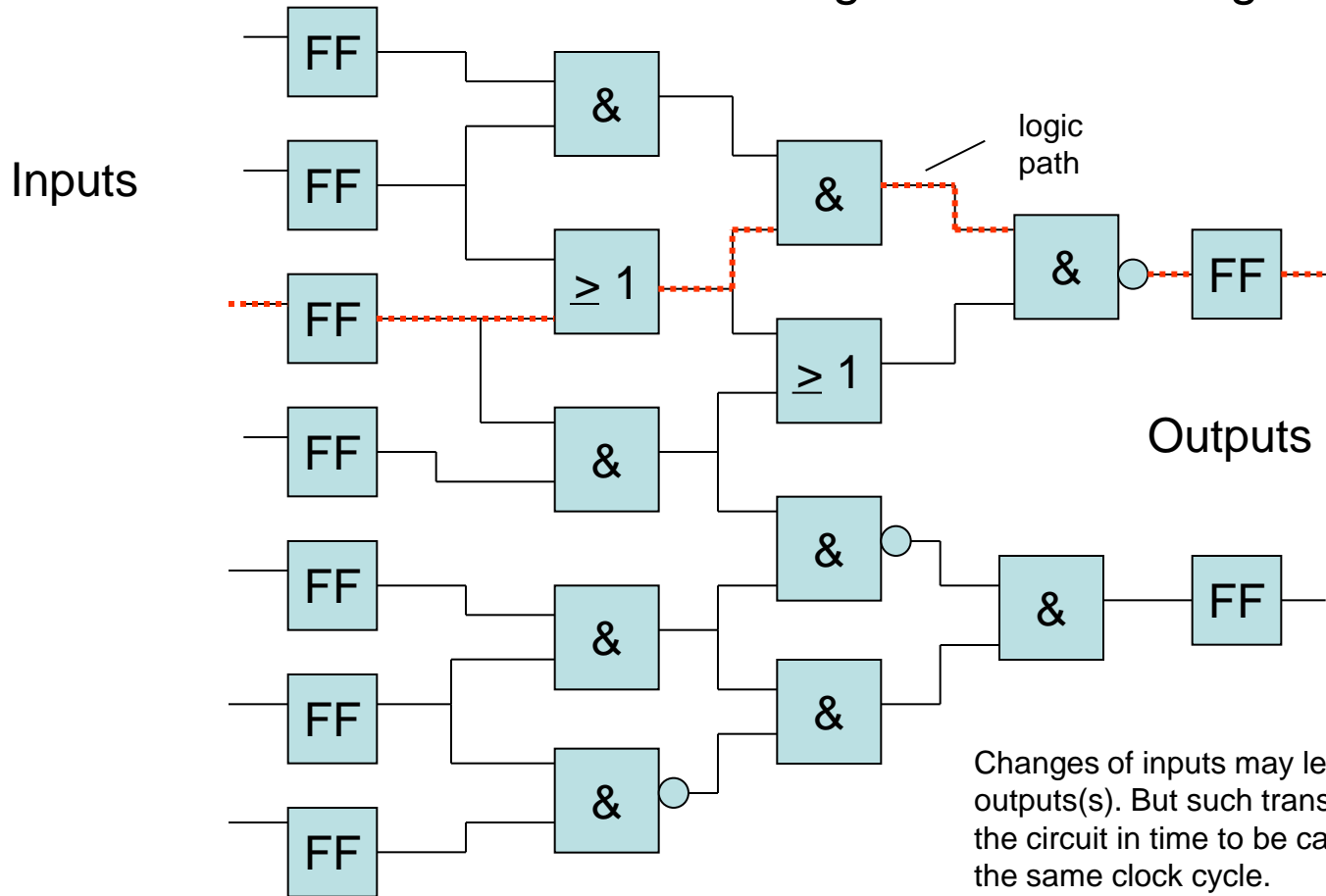


# Stuck-On- / Short -Fault



One transistor is always conducting. Leads to intermediate voltage levels.

# Logic-Structure / Logic Paths

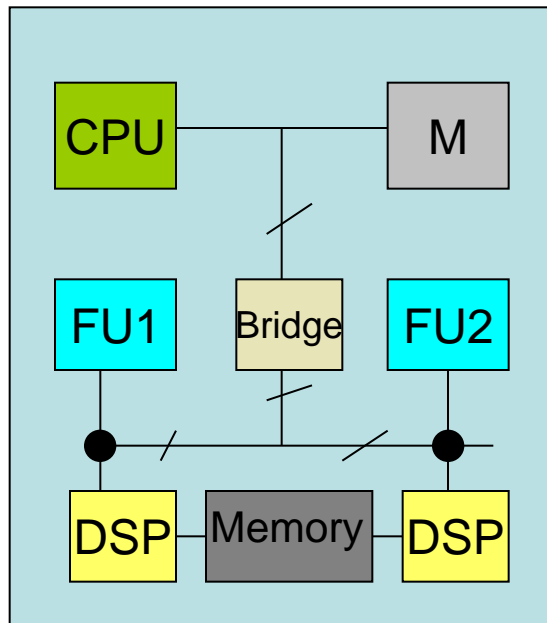


# Delay Faults

- Gate Delay Faults:  
Gates switch outputs too slowly. Reasons can be:  
Defects from manufacturing, aging, lower VDD because of „noise“.  
Almost untestable, since single gates can hardly be contacted for testing.
- Path Delay Faults:  
Switching of transitions along logic paths is too slow. Reasons can be gate-delay faults, but also EM-coupling and VDD-noise.
- Transition Faults: Logic gate outputs cannot be switched to opposite values via specific inputs. For example due to stuck-open or stuck-on transistors.

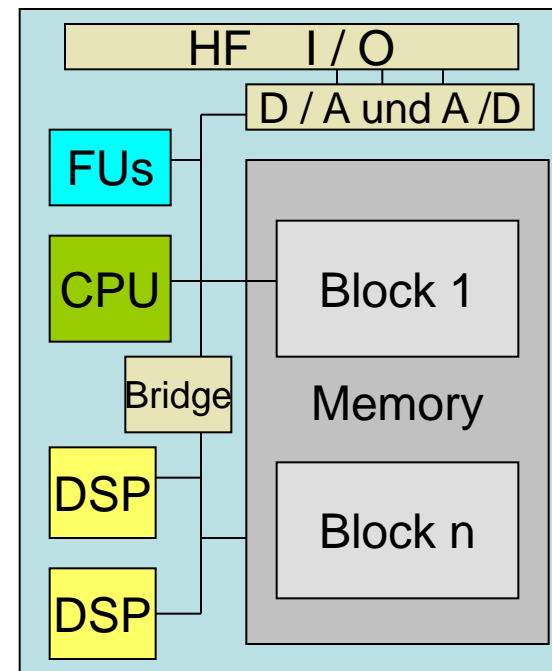
# Logic and Memory

SoC 2001



Memory-Share 10 – 30%

SoC 2015

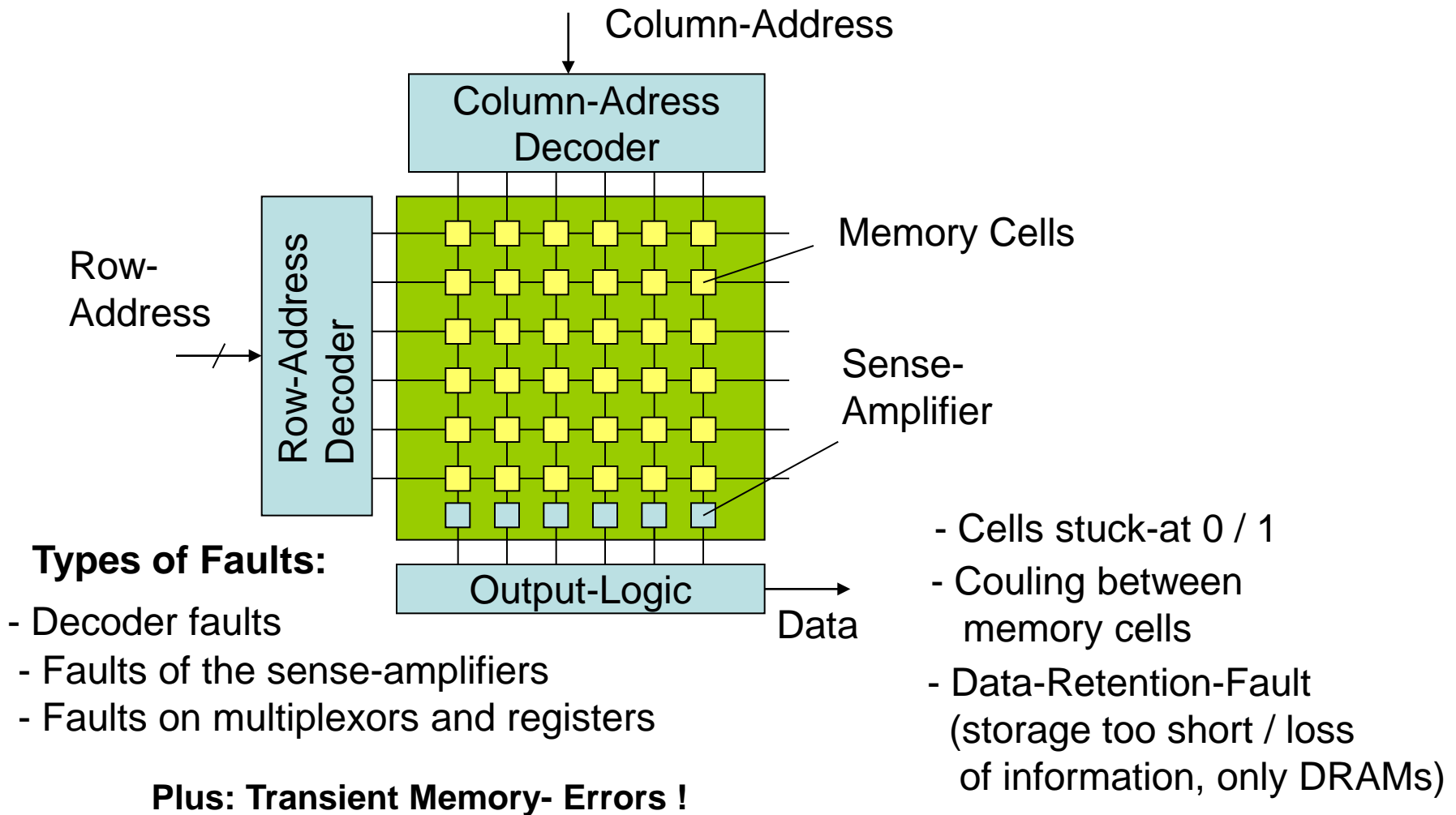


Memory-Share 50 bis 90 %



Memory faults get a dominating importance !

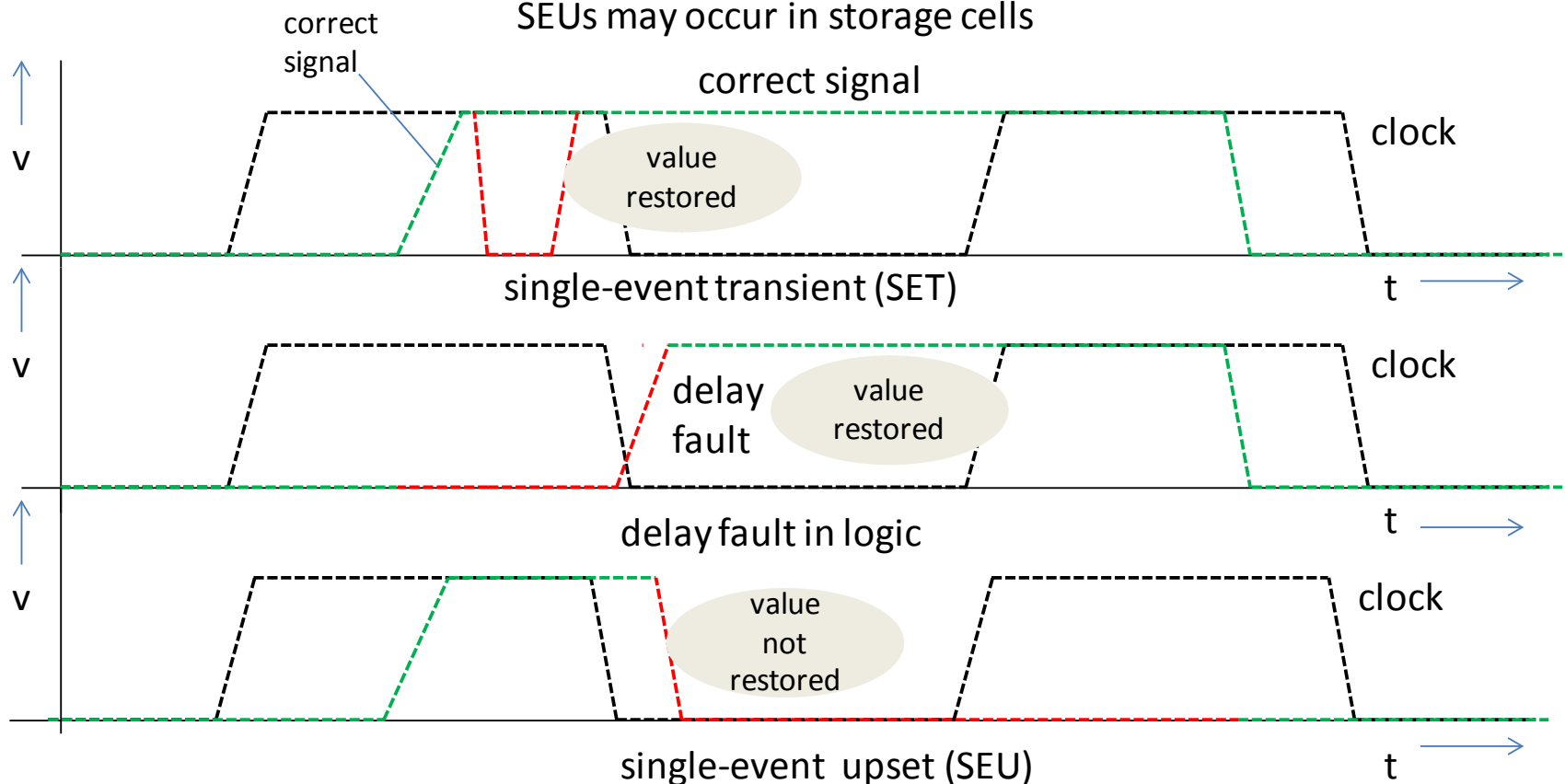
# Memory Faults



# Transient Faults and Delay Faults

SETs typically occur in logic

SEUs may occur in storage cells



Transient faults or SEUs that last longer than a clock cycle T are not detectable by most methods targeting SETs or delay faults !

# Transient Faults

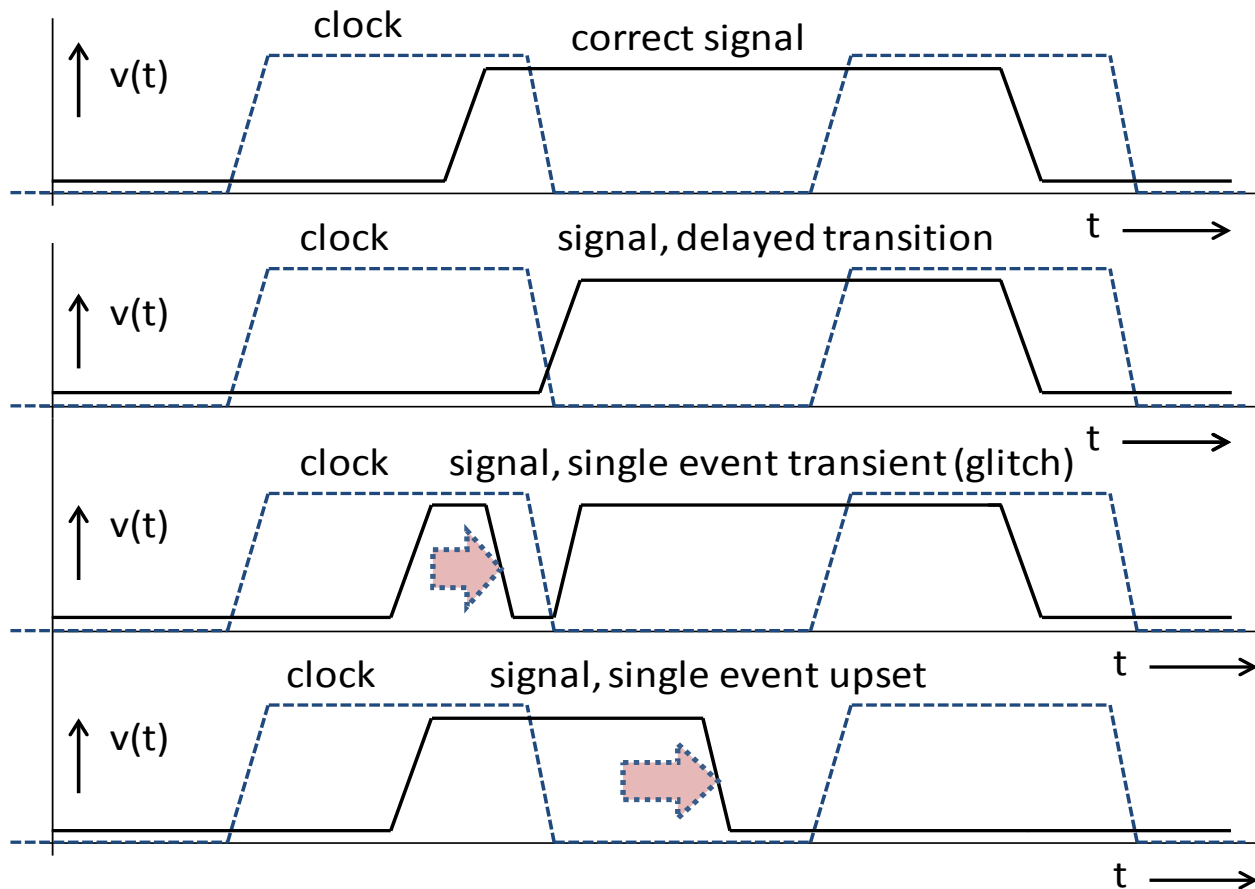
- Single event upset (SEU): A circuit node or storage cell changes status due to radiation.
- Multi-Event Upset (MEU): The same, but for several nodes / cells.

**... typically happens in storage nodes /flip-flops / memory cells.**

- Single event transients (SET): A circuit node gets the wrong opposite value, but returns to the correct value by itself.
- Multi-event transient (MET): The same, but for several nodes / cells.

**... this typically happens to nodes in CMOS logic. Also to flip-flops with „active“ inputs.**

# SEUs, SETs, Delay Faults



SET: Single Event Transient, returns to correct value. Typical in CMOS logic.

SEU: Single Event Upset, does not return to correct value. Typical in flip-flops and memory.

Also Multi-Event Transients (METs) and Multi-Event Upsets (MEUs) affecting more than one circuit node are common, but much less frequent !



# Software Faults

Software does not age by itself. Therefore software faults always come from faults in algorithms or in implementation.

Except for faulty specifications, faults in software may be found by formal methods. But this is practically possible only for relatively small (embedded!) pieces of software. Formal verification fails for large software units.

Pracitically, software is „validated“ by testing. This is not exhaustive.

Software-Funktion that are often used are well tested. However, in systems like cars, planes, trains etc. there is also software that is scarcely used, e. g. in order to handle exceptions and emergencies. This software is not that well-tested and typically exhibits errors just by the wrong time !

*Of course, faults in memory cells can affect software !! But here error correction coding (ECC) seems to work reasonably well !*